

Listing of Claims

Claims 1-15 have been cancelled.

16. (Currently Amended) A method of forming a shared global word line MRAM structure, comprising:
- etching a trench in an oxide layer formed over a substrate;
 - depositing an first liner material;
 - anisotropically [ansotropically] etching the deposited first liner material leaving the first liner material on edges of the trench, and physically contacting a bottom of the trench;
 - depositing an magnetic metal liner material;
 - anisotropically [ansotropically] etching the deposited magnetic metal liner material leaving the magnetic metal liner material over the first liner material on edges of the trench, so that the magnetic metal liner extends to and physically contacts the bottom of the trench;
 - depositing a conductive layer; and
 - chemically, mechanically polishing the conductive layer.
17. (Original) The method of forming a shared global word line MRAM structure of claim 16, wherein the first liner material comprises tantalum.
18. (Previously Presented) The method of forming a shared global word line MRAM structure of claim 16, wherein the magnetic metal liner material comprises at least one of Nickel, Chromium, Cobalt and Iron.
19. (Previously Presented) The method of forming a shared global word line MRAM structure of claim 16, wherein the conductive layer comprises Copper.

20. (Previously Presented) The method of forming a shared global word line MRAM structure of claim 16, wherein the conductive layer is deposited through chemical vapor deposition.
21. (Previously Presented) The method of forming a shared global word line MRAM structure of claim 16, wherein the substrate comprises a first MRAM array.
22. (Previously Presented) The method of forming a shared global word line MRAM structure of claim 21, further comprising forming a second MRAM array over the shared global word line.